

TCS800

800 Watts, 50 Volts, Pulsed Avionics 1030 MHz

GENERAL DESCRIPTION

The TCS800 is a high power COMMON BASE bipolar transistor. It is designed for pulsed systems in the frequency band 1030 MHz, with the pulse width and duty required for TCAS applications. The device has gold thin-film metallization and diffused ballasting for proven highest MTTF. The transistor includes input and output prematch for broadband capability. Low thermal resistance package reduces junction temperature, extends life.

CASE OUTLINE 55SM Style 1

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation

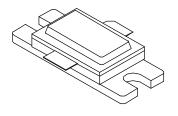
Device Dissipation @25°C¹ 1944 W

Maximum Voltage and Current

Collector to Base Voltage (BV_{ces}) 65 VEmitter to Base Voltage (BV_{ebo}) 3.5 VCollector Current (I_c) 50 A

Maximum Temperatures

Storage Temperature $-65 \text{ to } +200 \text{ }^{\circ}\text{C}$ Operating Junction Temperature $+230 \text{ }^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS @ 25°C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P _{out}	Power Out	F = 1030 MHz	800			W
Pin	Power Input	$V_{CC} = 50 \text{ Volts}$			126	W
P_{g}	Power Gain	$PW = 32 \mu sec$	8.0	9.0		dB
η_c	Collector Efficiency	DF = 1%		45		%
R_{L}	Input Return Loss			-12		dB
Pd	Pulse Droop			0.5		dB
VSWR	Load Mismatch Tolerance	F = 1030 MHz			4:1	

FUNCTIONAL CHARACTERISTICS @ 25°C

BV _{ebo} *	Emitter to Base Breakdown	Ie = 70 mA	3.5		V
$\mathrm{BV}_{\mathrm{ces}}$	Collector to Emitter Breakdown	Ic = 100 mA	65		V
h _{FE} *	DC – Current Gain	Vce = 5V, Ic = 5A	20		
θjc^1	Thermal Resistance			0.09	°C/W

NOTE 1: At rated output power and pulse conditions.

*: Not measurable due to internal EB returns

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Freq (MHz)	Zin	Zcl
1030	1.63+j1.59	0.47-j1.14

